

November 2013

FQI5N60C

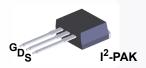
N-Channel QFET $^{\rm @}$ MOSFET 600 V, 4.5 A, 2.5 Ω

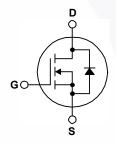
Features

- 4.5 A, 600 V, $R_{DS(on)}$ = 2.5 Ω (Max.) @V_{GS} = 10 V, I_D = 2.1 A
- Low Gate Charge (Typ. 15 nC)
- Low Crss (Typ. 6.5 pF)
- · 100% Avalanche Tested

Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQI5N60CTU	Unit
V_{DSS}	Drain-Source Voltage		600	V
I _D	Drain Current - Continuous (T _C = 25°C)		4.5	А
	- Continuous (T _C = 100°C)		2.6	Α
I _{DM}	Drain Current - Pulsed	(Note 1)	18	А
V _{GSS}	Gate-Source Voltage		± 30	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		210	mJ
I _{AR}	Avalanche Current	(Note 1)	4.5	Α
E _{AR}	Repetitive Avalanche Energy (N		10	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5	V/ns
D_	Power Dissipation (T _C = 25°C)		100	W
P_{D}	- Derate above 25°C		0.8	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C	

Thermal Characteristics

Symbol	Parameter	FQI5N60CTU	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max. 1.25		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	C/VV

Package Marking and Ordering Information

Device Marking Device		Package	Package Reel Size		Quantity	
FQI5N60C	FQI5N60CTU	5N60CTU I ² -PAK		N/A	50 units	

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	racteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	600			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.6		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 600 V, V _{GS} = 0 V			1	μΑ
		V _{DS} = 480 V, T _C = 125°C			10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 2.25 A		2.0	2.5	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 2.25 A		4.7		S
C _{iss}	ic Characteristics Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V,		515	670	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		55	72	pF
C _{rss}	Reverse Transfer Capacitance			6.5	8.5	pF
Switchi	ng Characteristics					
t _{d(on)}	Turn-On Delay Time	V = 200 V I = 4.5A		10	30	ns
t _r	Turn-On Rise Time	V_{DD} = 300 V, I_{D} = 4.5A, R_{G} = 25 Ω		42	90	ns
t _{d(off)}	Turn-Off Delay Time	11.G - 20 32		38	85	ns
t _f	Turn-Off Fall Time	(Note 4)		46	100	ns
Qg	Total Gate Charge	V _{DS} = 480 V, I _D = 4.5A,	/	15	19	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V		2.5		nC
Q _{gd}	Gate-Drain Charge	(Note 4)		6.6	/	nC
Drain-S	ource Diode Characteristics a	nd Maximum Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				4.5	Α
I _{SM}	Maximum Pulsed Drain-Source Diode F	Forward Current			18	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 4.5 A			1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 4.5 A,		300		ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs		2.2		μС

NOTES:

^{1.} Repetitive Rating : Pulse width limited by maximum junction temperature.

^{2.} L = 18.9 mH, I_{AS} = 4.5 A, V_{DD} = 50V, R_G = 25 Ω , starting T_J = 25°C.

 $^{3.~}I_{SD} \leq 4.5~A,~di/dt \leq 200~A/\mu s,~V_{DD} \leq BV_{DSS,}~starting~~T_J = 25^{\circ}C.$

^{4.} Essentially independent of operating temperature.

Typical Characteristics

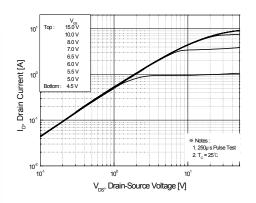


Figure 1. On-Region Characteristics

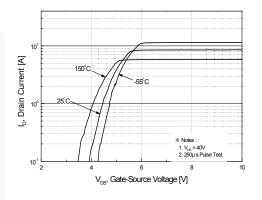


Figure 2. Transfer Characteristics

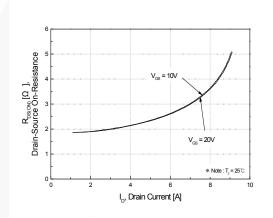


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

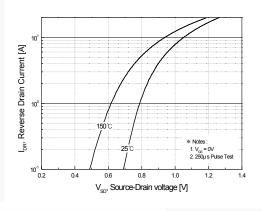


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

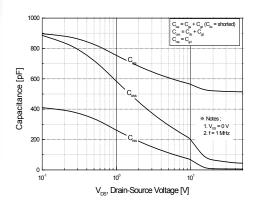


Figure 5. Capacitance Characteristics

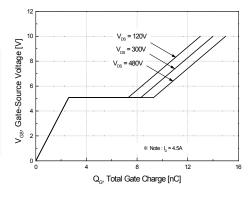


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

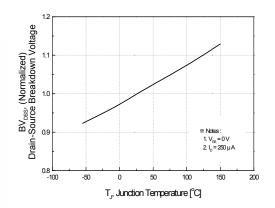
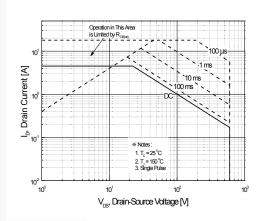


Figure 7. Breakdown Voltage Variation vs Temperature





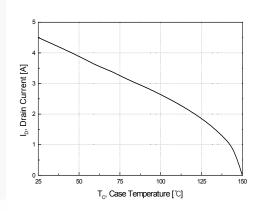


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs Case Temperature

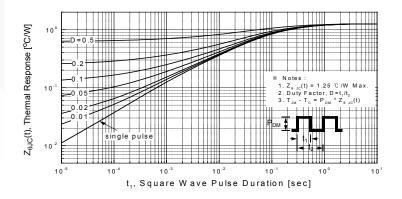


Figure 11. Transient Thermal Response Curve

Figure 12. Gate Charge Test Circuit & Waveform

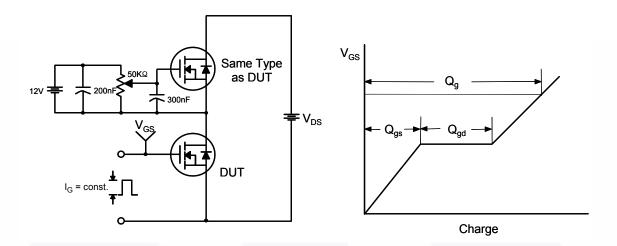


Figure 13. Resistive Switching Test Circuit & Waveforms

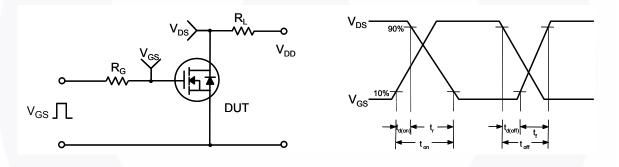
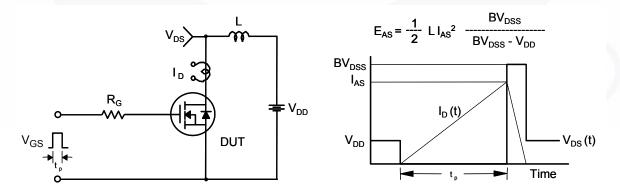


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



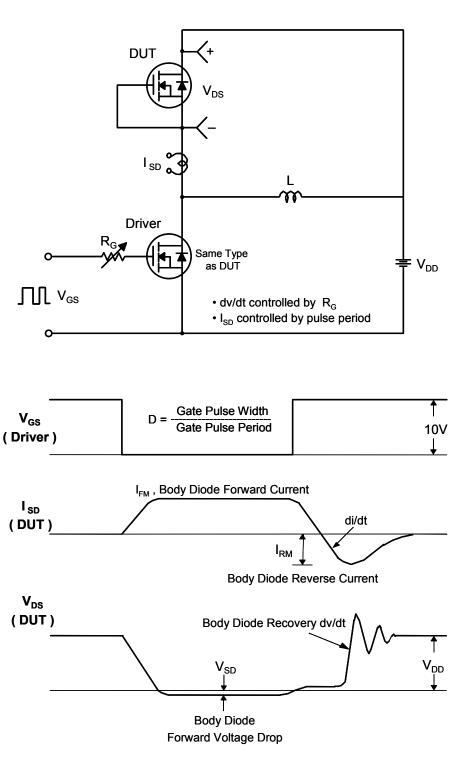


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

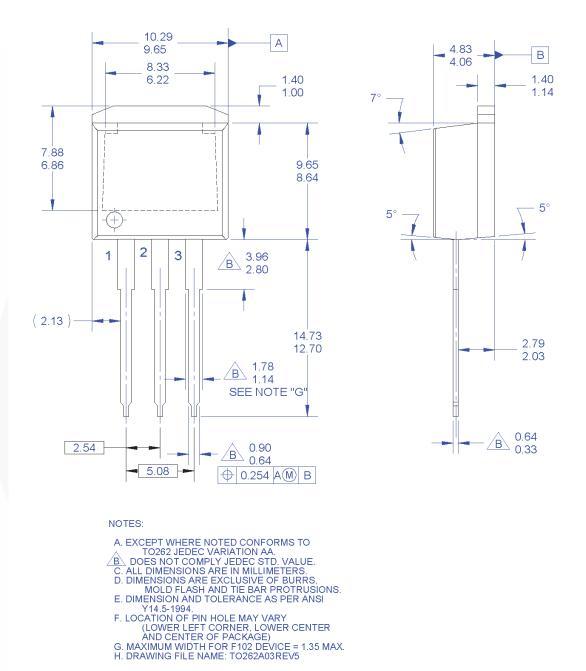


Figure 16. TO262 (I²PAK), Molded, 3-Lead, Jedec Variation AA

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